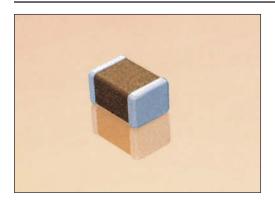
X5R Dielectric



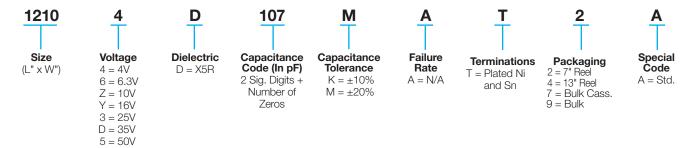
General Specifications



GENERAL DESCRIPTION

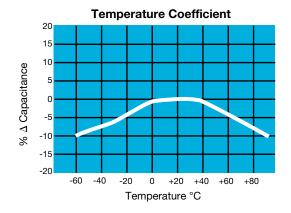
- General Purpose Dielectric for Ceramic Capacitors
- EIA Class II Dielectric
- Temperature variation of capacitance is within ±15% from -55°C to +85°C
- Well suited for decoupling and filtering applications
- Available in High Capacitance values (up to 100μF)

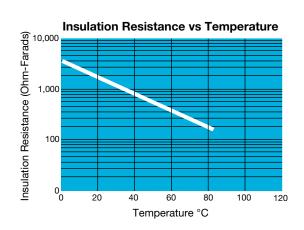
PART NUMBER (see page 2 for complete part number explanation)



NOTE: Contact factory for availability of Tolerance Options for Specific Part Numbers. Contact factory for non-specified capacitance values.

TYPICAL ELECTRICAL CHARACTERISTICS





X5R Dielectric



Specifications and Test Methods

	ter/Test	X5R Specification Limits	Measuring Conditions								
	perature Range	-55°C to +85°C	Temperature C	Cycle Chamber							
Capac	on Factor	Within specified tolerance ≤ 2.5% for ≥ 50V DC rating ≤ 3.0% for 25V DC rating ≤ 12.5% Max. for 16V DC rating and lower Contact Factory for DF by PN	Freq.: 1.0 kHz ± 10% Voltage: 1.0Vrms ± .2V For Cap > 10 μF, 0.5Vrms @ 120Hz								
Insulation	Resistance	10,000MΩ or 500MΩ - μF, whichever is less	120 ± 5 secs @ ro	h rated voltage for om temp/humidity							
Dielectric	Strength	No breakdown or visual defects	limited to 5	e and discharge current 0 mA (max)							
	Appearance	No defects		on: 2mm							
Resistance to	Capacitance Variation	≤ ±12%	Test Time: 30 seconds 1mm/sec								
Flexure Stresses	Dissipation Factor	Meets Initial Values (As Above)									
	Insulation Resistance	≥ Initial Value x 0.3	90 mm —								
Solde	rability	≥ 95% of each terminal should be covered with fresh solder	Dip device in eutection for 5.0 ± 0	c solder at 230 ± 5°C .5 seconds							
	Appearance	No defects, <25% leaching of either end terminal									
	Capacitance Variation	≤ ±7.5%	Dip device in eutectic solder at 260°C for 60 seconds. Store at room temperature for 24 ± 2 hours before measuring electrical properties.								
Resistance to Solder Heat	Dissipation Factor	Meets Initial Values (As Above)									
	Insulation Resistance	Meets Initial Values (As Above)	hours before measurin	ig electrical properties.							
	Dielectric Strength	Meets Initial Values (As Above)									
	Appearance	No visual defects	Step 1: -55°C ± 2°	30 ± 3 minutes							
	Capacitance Variation	≤ ±7.5%	Step 2: Room Temp	≤ 3 minutes							
Thermal Shock	Dissipation Factor	Meets Initial Values (As Above)	Step 3: +85°C ± 2°	30 ± 3 minutes							
Gilden	Insulation Resistance	Meets Initial Values (As Above)	Step 4: Room Temp ≤ 3 minutes								
	Dielectric Strength	Meets Initial Values (As Above)	Repeat for 5 cycles and measure after 24 ± 2 hours at room temperature								
	Appearance	No visual defects	Charge device with	<u> </u>							
	Capacitance Variation	≤ ±12.5%	test chamber set at 85°C ± 2°C for 1000 hours (+48, -0). Note: Contact factory for *optional specification part numbers that are tested at < 1.5X rated voltage. Remove from test chamber and stabilize at room temperature for 24 ± 2 hours before measuring.								
Load Life	Dissipation Factor	≤ Initial Value x 2.0 (See Above)									
	Insulation Resistance	≥ Initial Value x 0.3 (See Above)									
	Dielectric Strength	Meets Initial Values (As Above)									
	Appearance	No visual defects	Store in a test chamb	er set at 85°C ± 2°C/							
local	Capacitance Variation	≤ ±12.5%	85% ± 5% relative hu (+48, -0) with rate	midity for 1000 hours							
Load Humidity	Dissipation Factor	≤ Initial Value x 2.0 (See Above)	Remove from chamber and stabilize at room temperature and humidity for 24 ± 2 hours before measuring.								
	Insulation Resistance	≥ Initial Value x 0.3 (See Above)									
	Dielectric Strength	Meets Initial Values (As Above)									



X5R Dielectric





PREFERRED SIZES ARE SHADED

																	=																											
SIZ	Έ	01	01*		(020	1	0402						0603							0805						1206						1210					1812						
Solde	ring	Reflo	v Only	T	Ref	low (Only	,	Reflow/Wave						Reflow/Wave								low/	Nave		Reflow/Wave						Reflow Only						Reflow Only						
Packa	ging		mbossed			l Pap			All Paper					All Paper								Paper/Embossed						Paper/Embossed						Paper/Embossed					All Embossed					
(L) Length	mm (in.)	0.40 : (0.016 ±				0 ± 0 4 ± 0		,	1.00 ± 0.10 (0.040 ± 0.004)					1.60 ± 0.15 (0.063 ± 0.006)							2.01 ± 0.20 (0.079 ± 0.008)						3.20 ± 0.20 (0.126 ± 0.008)						3.20 ± 0.20 (0.126 ± 0.008)						4.50 ± 0.30 (0.177 ± 0.012)					
(W) Width	mm	0.20 :	± 0.02	T	0.3	0 ± 0	0.03			0.50	± 0.1	0				0.8	1 ± 0.	.15		+	1.25 ± 0.20 1.60 ± 0.20									2.50 ± 0.20					\neg	3.20 ± 0.20 (0.126 ± 0.008)								
	(in.) mm	(0.008 ±		⊢		1 ± 0 5 ± 0)	(0.00 ± 0.00		_				2 ± 0.5 5 ± 0.5			4	(0.049 ± 0.008) 0.50 ± 0.25					(0.063 ± 0.008) 0.50 ± 0.25								.098 ±		3)	\dashv		6 ± 0 1 ± 0					
(t) Terminal	(in.)	(0.004 :			(0.006 ± 0.002)					0.010	0.0 ± 0.0	006)				(0.01	4 ± 0 .	.006)				(0.0	20 ± 1	0.010)			(0.020 ± 0.010) 3.3 10 16 25 35 50 10					(0.020 ± 0.010)					(0.024 ± 0.014)							
	WVDC	6.3	10	4	6.3	10	16		4 6	3 10	16	25	50	4	6.3	10	16	25	35 8	50	6.3	10	16 2	25 35	5 50	6.3	10	16 2	5 35	50	100	4	6.3 1	10 16	25	35	50	6.3 1	0 25	50				
Cap (pF)	100 150		B B	ı				A A												-																								
(pr)	220		В	ı				A					С							-																								
	330		В	Т				Α		T	1		С					\exists	1	7		1	1			T	П					>	_	_	< 1/	۸,				\top				
	470		В	ı				Α					С							-										•	_Ľ		_	\sim	≺	\ ≥	\leq							
	680		В	H				A		+	+		С					_	_	4	+	_	+	+	-	╀		_			\bigcap	\sim	\mathcal{L}			ノ、	ĴТ	-		_				
	1000 1500	В	B B	ı			A A	A A					C							-											_	_					_							
	2200	В	В	ı		Α	Α	Α					С							-													4											
	3300	В	В			Α	Α	Α					С				П			T						Т							"											
	4700	В	В	ı		A	A	A	C											G																								
Con	6800	В	B B	⊢		A	A	A		+	+	С	Н					_	_	G G	+	+	+			╁		_		-		Н					Н	+		+				
Cap (µF)	0.010 0.015	В	Б	١.		А	A	А				C						G		G																								
· · · /	0.022	В			A*						С	C						G		G					Ν																			
	0.033	В									С							G		G					N													П		П				
	0.047 0.068	B B		l	A*						C	С						G G		G G					N N																			
	0.10	В		┢	A*			\dashv		С		С						G	_	G	+	+		N	N	-		+	+			Н	+		\vdash		Н	\pm		+				
	0.15			l														G		u				N N		1																		
	0.22			Α*	A*				C	* C	* C*						-	G		4				N N						Q										\perp				
	0.33								0+ 0									G		-				N																				
	0.47 0.68			A^	A*				C* C	^ C	. C.						G G			-				N N				(Q								Χ							
	1.0			A*	A*				C* C	* C	* C*		Н		G	G		J*	+	+	+		_	N	P*			(QQ		Q	Н	+		Х	Х	Х	\pm	+	+				
	1.5														-	-				-						1				1														
	2.2			Α*	A*				C* C	* C	*		Ш	G*	G*	J*	J*		_	4	_	_	N	N	_	L		Q	2		Q	Ш	4	_	Z	Х	Ш	4	_	_				
	3.3 4.7			l					E* E	*				J* J*	J* J*	J* J*	J*					N N I	N* 1	. *		Q	QQ	Q		Q				Q	Z									
	10			l										K	J*	J*							N* 1	*		Q	Q	Q		Q				x Z					Z					
	22			Г										K						T	N*	*				Q*	Q*	Q*					Z .	z z	Z*		П	\top						
	47			l																	±					Q*						_	Z*											
	100 WVDC	6.3	10	4	6.3	10	16	25	4 6.	3 10) 16	25	50	4	6.3	10	16	25	35 5	50	6.3	10	16 2	25 35	5 50	6.3	10	16 2	5 35	50	100	4	Z* 6.3 1	10 16	25	35	50	6.3	0 25	5 50				
SIZ			1101* 0201				25 4 6.3 10 16 25 5 0402						0.0		0603		00 0		0.01		080		7 00	0.0	10	12		100	1100		4 6.3 10 16 25 35 5 1210			- 00	50 6.3 10 25 50 1812									
1.44								E			^						1/						N.I.					^			\/													
Letter Max.	0.33	3	B 0.22	H					1	- (G 0.90	+	0	J).94		1	K 1.02	+		M .27	+		.40	+	1.5			Q 1.78	_		X .29		2.5		2	Z 2.79								
Thickness			0.22												0.035	j)		.037			.040)		. <i>21</i> 050))		.40)	(0.0)		(0.070			.20 090))	(0.10			.110				
															EMBOSSED																													



= *Optional Specifications - Contact factory

NOTE: Contact factory for non-specified capacitance values

*EIA 01005

